

Product Summary

BV_{DSS}	$R_{DS(ON)} \text{ Max}$	$I_D \text{ Max}$ $T_A = +25^\circ\text{C}$
60V	0.08Ω @ $V_{GS} = 10\text{V}$	5.3A
	0.15Ω @ $V_{GS} = 4.5\text{V}$	2.8A

Features and Benefits

- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)
- The ZXMN6A08GQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

<https://www.diodes.com/quality/product-definitions/>

Description and Applications

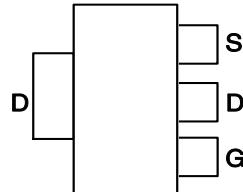
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- BLDC motors
- DC-DC converters
- Load switches

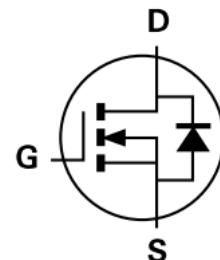
SOT223 (Type ZN)



Top View



Pinout - Top View



Equivalent Circuit

Ordering Information (Note 4)

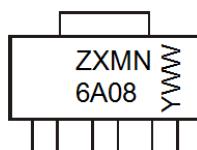
Orderable Part Number	Package	Packing	
		Qty.	Carrier
ZXMN6A08GQTA	SOT223 (Type ZN)	1000	Tape & Reel
ZXMN6A08GQTC	SOT223 (Type ZN)	4000	Tape & Reel

Notes:

- EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

SOT223 (Type ZN)



ZXMN6A08 = Product Type Marking Code
 YWW = Date Code Marking
 Y = Last Digit of Year (ex: 4 = 2024)
 WW = Week Code (01 to 53)

Maximum Ratings

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current @ V _{GS} = 10V	I _D	5.3	A
		4.2	A
		3.8	A
Pulsed Drain Current (Note 7)	I _{DM}	20	A
Continuous Source Current (Body Diode) (Note 5)	I _S	2.1	A
Pulsed Source Current (Body Diode) (Note 7)	I _{SM}	20	A
Power Dissipation at T _A = +25°C (Note 6)	P _D	2	W
Linear Derating Factor		16	mW/°C
Power Dissipation at T _A = +25°C (Note 5)	P _D	3.9	W
Linear Derating Factor		31	mW/°C
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

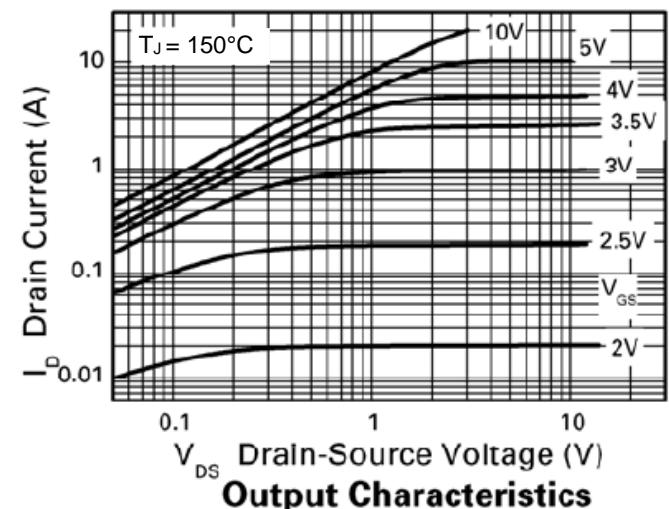
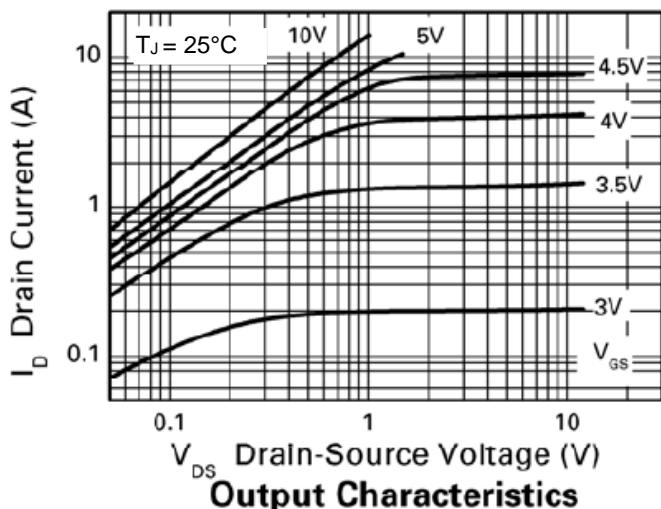
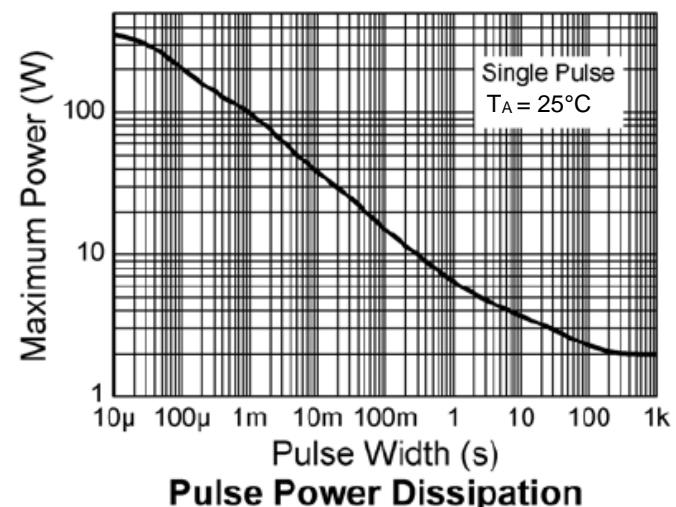
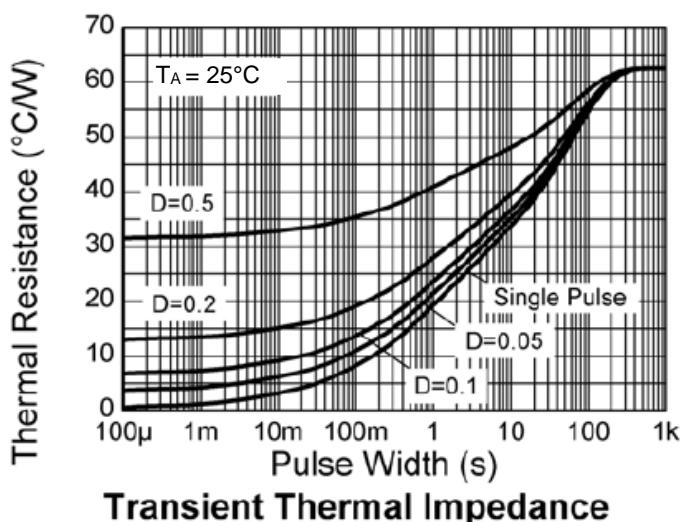
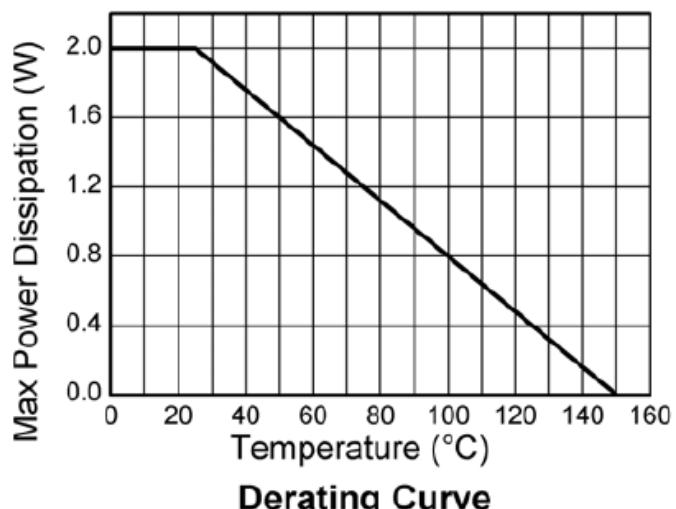
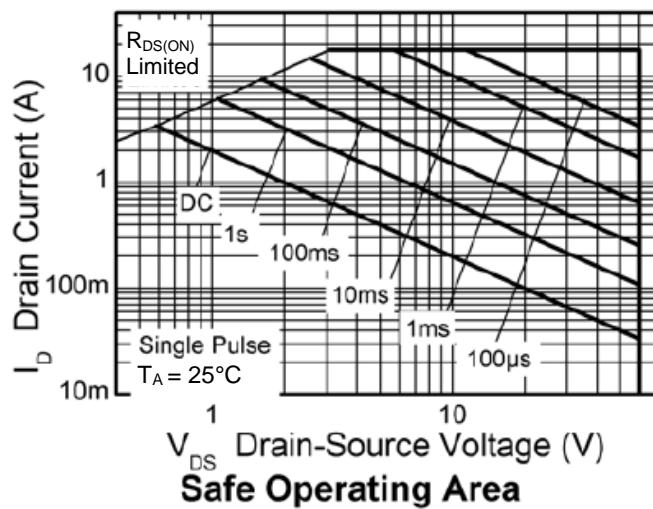
Characteristic	Symbol	Value	Unit
Junction to Ambient (Note 6)	R _{θJA}	62.5	°C/W
Junction to Ambient (Note 5)	R _{θJA}	32	°C/W

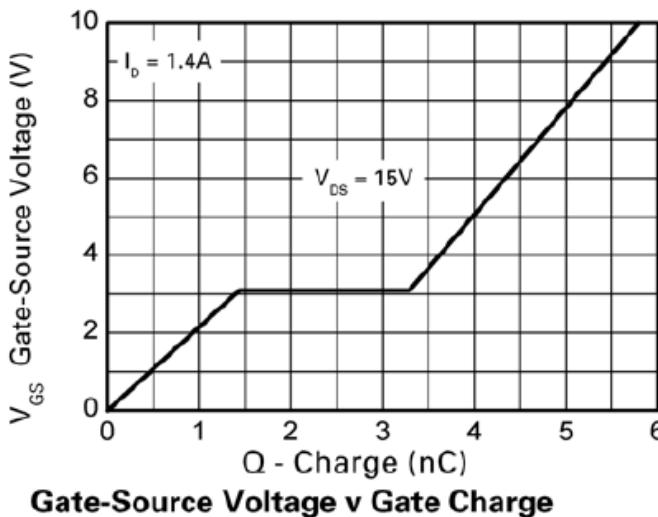
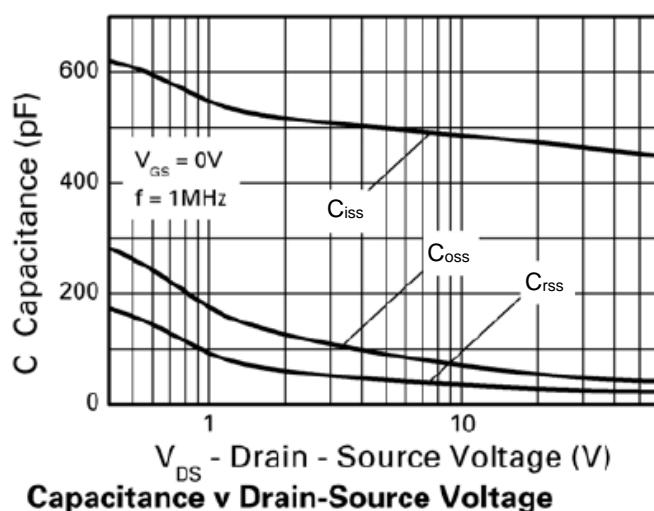
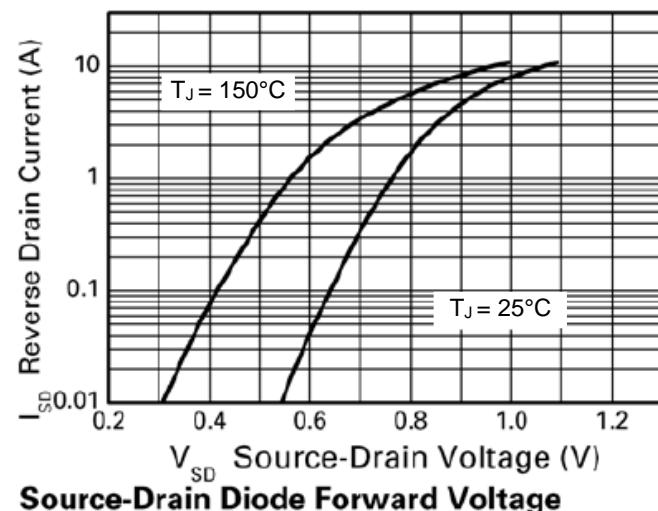
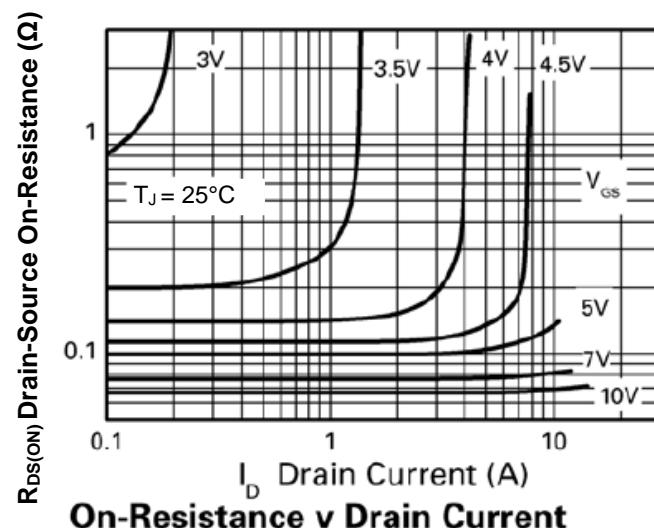
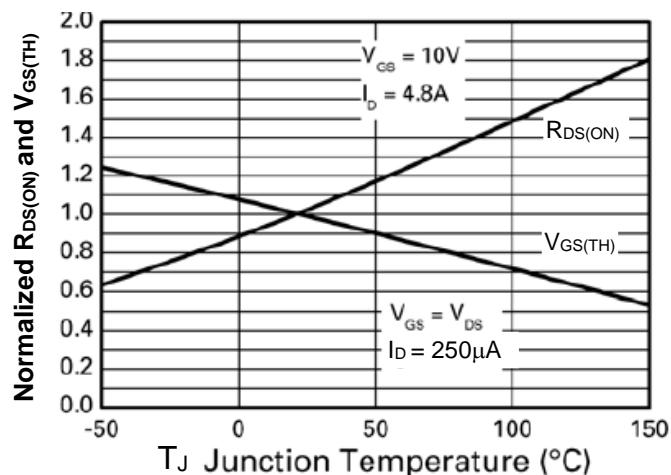
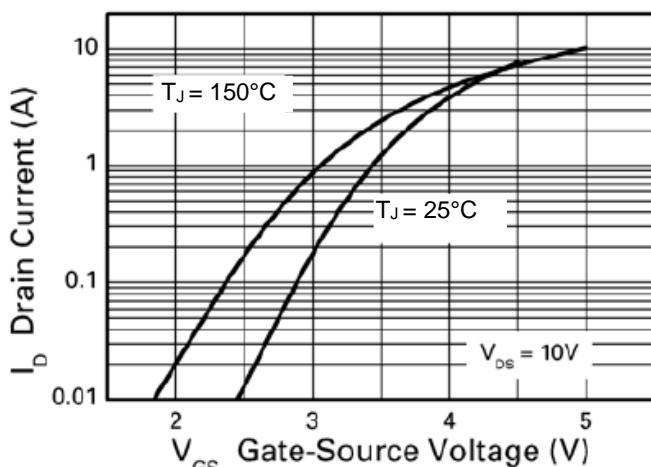
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	0.5	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	1	—	—	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-State Resistance	R _{D(S)}	—	0.06	0.08	Ω	V _{GS} = 10V, I _D = 4.8A
		—	0.08	0.15	Ω	V _{GS} = 4.5V, I _D = 4.2A
Forward Transconductance (Note 8)	g _{fs}	—	6.6	—	S	V _{DS} = 15V, I _D = 4.8A
Diode Forward Voltage	V _{SD}	—	0.88	1.2	V	T _J = +25°C, I _S = 4A V _{GS} = 0V
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	459	—	pF	V _{DS} = 40V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	44.2	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	24.1	—	pF	
Turn-On Delay Time (Note 9)	t _{D(ON)}	—	2.6	—	ns	V _{DD} = 30V, I _D = 1.5A R _G ≥ 6.0Ω, V _{GS} = 10V
Turn-On Rise Time (Note 9)	t _R	—	2.1	—	ns	
Turn-Off Delay Time (Note 9)	t _{D(OFF)}	—	12.3	—	ns	
Turn-Off Fall Time (Note 9)	t _F	—	4.6	—	ns	
Gate Charge (Note 9)	Q _G	—	4.0	—	nC	V _{DS} = 30V, V _{GS} = 5V I _D = 1.4A
Total Gate Charge (Note 9)	Q _G	—	5.8	—	nC	V _{DS} = 30V, V _{GS} = 10V I _D = 1.4A
Gate-Source Charge (Note 9)	Q _{GS}	—	1.4	—	nC	
Gate Drain Charge (Note 9)	Q _{GD}	—	1.9	—	nC	
SOURCE-DRAIN DIODE						
Reverse-Recovery Time (Note 8)	t _{RR}	—	19.2	—	ns	T _J = +25°C, I _S = 1.4A
Reverse-Recovery Charge (Note 8)	Q _{RR}	—	30.3	—	nC	di/dt = 100A/μs

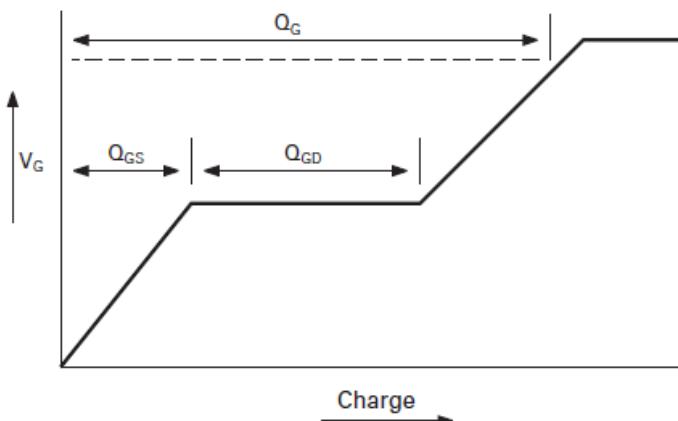
Notes:

5. For a device surface-mounted on FR-4 PCB measured at t ≤ 10s.
6. For a device surface-mounted on 25mm × 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.
7. Repetitive rating - 25mm × 25mm FR-4 PCB, D = 0.02, pulse width 300μs - pulse width limited by maximum junction temperature.
8. For design aid only, not subject to production testing.
9. Switching characteristics are independent of operating junction temperature.

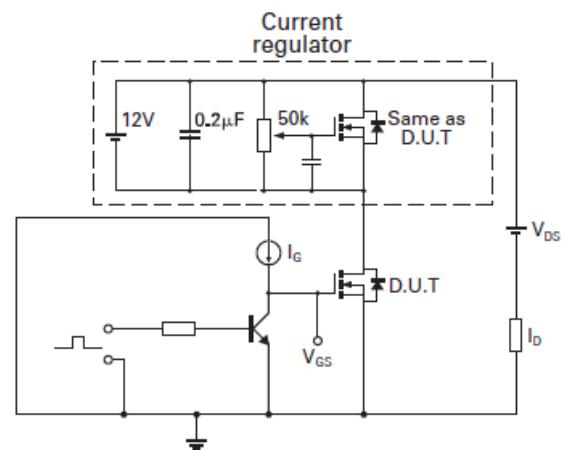




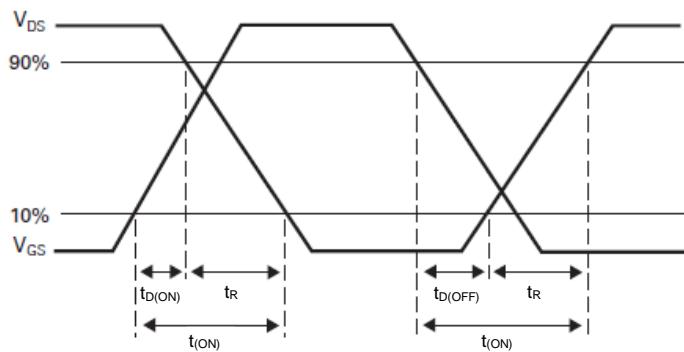
Test Circuits



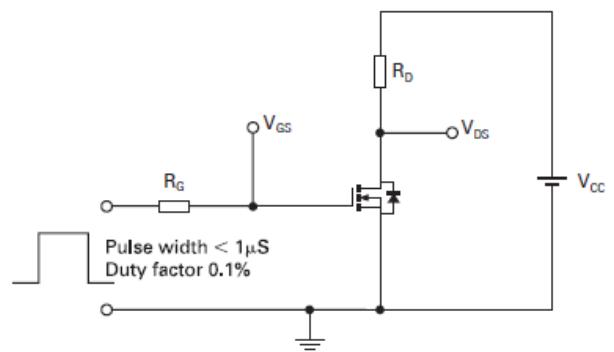
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

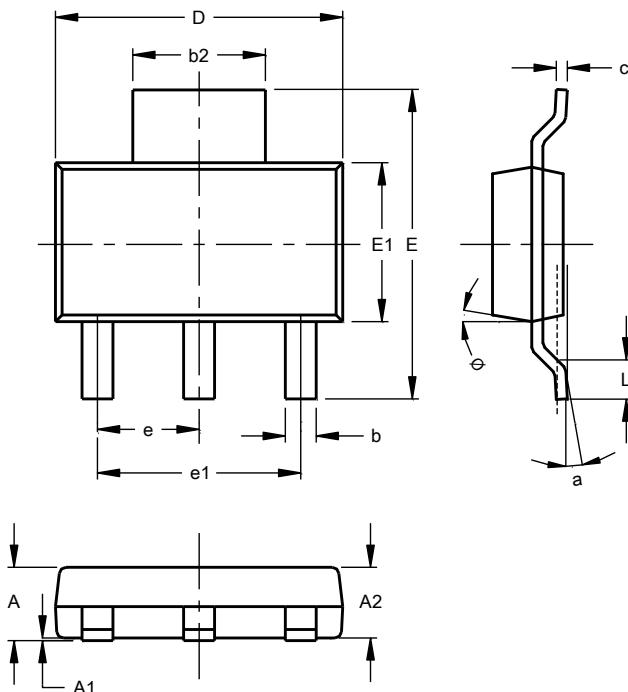


Switching time test circuit

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223 (Type ZN)



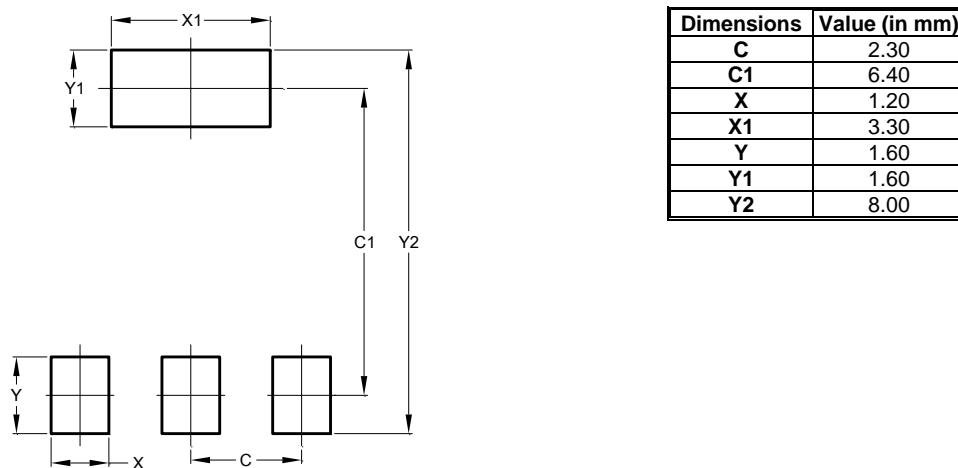
SOT223 (Type ZN)			
Dim	Min	Max	Typ
A	--	1.70	--
A1	0.02	0.10	--
A2	1.50	1.68	1.60
b	0.60	0.80	--
b2	2.90	3.10	--
c	0.24	0.32	--
D	6.30	6.70	--
E	6.70	7.30	--
E1	3.30	3.70	--
e	2.30 NOM		
e1	4.60 NOM		
L	0.90	--	--
a	--	--	10°
θ	--	15°	--

All Dimensions in mm

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223 (Type ZN)



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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